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REPLY UNDER 37 C.F.R. § 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER ART UNIT 2811

#12/B (NE)  
4/28/3  
Suresh

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
OHMI *et al.*

Application No.: 09/866,576

Filed: May 29, 2001

Title: SEMICONDUCTOR DEVICE FORMED ON (111)  
SURFACE OF A Si CRYSTAL AND FABRICATION PROCESS  
THEREOF

Confirmation No. 4482

ART UNIT: 2811

Examiner: OWEN S. D.

RECEIVED  
APR 25 2003  
TECHNOLOGY CENTER 2800

\* \* \* \*

April 23, 2003

AMENDMENT AFTER FINAL UNDER 37 C.F.R. § 1.116

Hon. Commissioner of Patents  
Washington, DC 20231

Sir:

Responsive to the Office Action dated January 30, 2003, please amend the above  
identified application as follows:

IN THE CLAIMS

Please amend claim 1 as follows:

1. (Twice Amended) A semiconductor device comprising:
- a Si crystal having a (111) surface; and
- an insulation film formed on said (111) surface of said Si crystal,
- wherein at least a part of said insulation film comprises a Si oxide film containing Kr,
- said Si oxide film being substantially free from crystal defects.

04/24/2003 RMEBRAHT 00000034 033975 09866576

01 FC:1201 168.00 CH  
02 FC:1202 144.00 CH